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# LF411JAN Low Offset, Low Drift JFET Input Operational Amplifier

Check for Samples: LF411JAN

### **FEATURES**

Internally Trimmed Offset Voltage: 0.5 mV(Typ)

• Input Offset Voltage Drift: 30 μV/°C

Low Input Bias Current: 50 pA

Low Input Noise Current: 0.01 pA/√Hz

Wide Gain Bandwidth: 3 MHz Typ.

High Slew Rate: 7V/μs (Min.)

Low Supply Current: 1.8 mA

• High Input Impedance: 10<sup>12</sup>Ω

• Low Total Harmonic Distortion:  $A_V = 10$ ,  $R_L = 10 K\Omega$ ,  $V_O = 20 V_{P-P}$ , BW = 20 Hz - 20 kHz < 0.02%

Low 1/f Noise Corner: 50 Hz

Fast Settling Time to 0.01%: 1.5 μs

## **Connection Diagram**

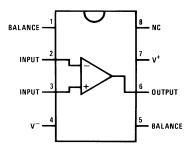


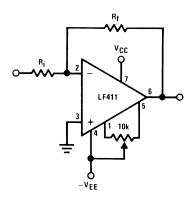
Figure 1. 8LD Ceramic Dual-in Line Package See Package Number NAB0008A (Top View)

### DESCRIPTION

This device is a low cost, high speed, JFET input operational amplifier with very low input offset voltage and ensured input offset voltage drift. It requires low supply current yet maintains a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF411 is pin compatible with the standard LM741 allowing designers to immediately upgrade the overall performance of existing designs.

This amplifier may be used in applications such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage and drift, low input bias current, high input impedance, high slew rate and wide bandwidth.

## **Typical Connection**



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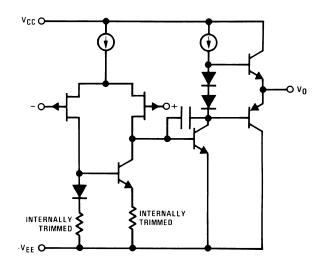
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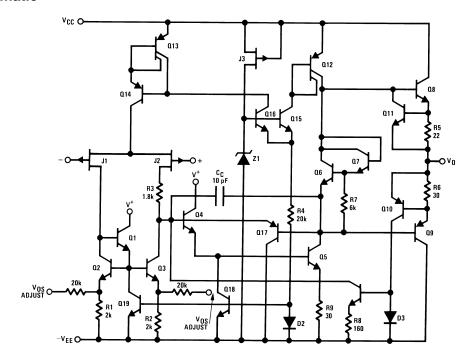
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## **Simplified Schematic**



### **Detailed Schematic**





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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## Absolute Maximum Ratings<sup>(1)</sup>

Supply Voltage	±18V					
Differential Input Voltage	±30V					
Input Voltage Range (2)	±15V					
Output Short Circuit Duration			Continuous			
Power Dissipation (3)(4)			400mW			
T <sub>Jmax</sub>	T <sub>Jmax</sub>					
	0	Still Air	162°C/W			
Thermal Resistance	$\theta_{JA}$	400LF/Min Air Flow	65°C/W			
	$\theta_{JC}$	20°C/W				
Operating Temperature Range	Operating Temperature Range					
Storage Temperature Range	-65°C ≤ T <sub>A</sub> ≤ 150°C					
Lead Temperature (Soldering, 10	300°C					
Package Weight (Typical)	TBD					
ESD Tolerance <sup>(5)</sup>	750V					

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not ensure specific performance limits. For ensured specifications and test conditions, see the Electrical Characteristics. The specified specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.
- Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.
- The maximum power dissipation must be derated at elevated temperatures and is dictated by T<sub>Jmax</sub> (maximum junction temperature),  $\theta_{JA}$  (package junction to ambient thermal resistance), and  $T_A$  (ambient temperature). The maximum allowable power dissipation at any temperature is  $P_{Dmax} = (T_{Jmax} - T_A)/\theta_{JA}$  or the number given in the Absolute Maximum Ratings, whichever is lower. Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the
- part to operate outside specified limits.
- (5) Human body model, 100pF discharged through 1.5KΩ.

## **Quality Conformance Inspection**

Table 1. Mil-Std-883, Method 5005 - Group A

Subgroup	Description	Temp °C
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55
12	Settling time at	25
13	Settling time at	125
14	Settling time at	-55



### **Electrical Characteristics DC Parameters**

The following conditions apply to all the following parameters, unless otherwise specified.

DC:  $V_{CC} = \pm 15V$ ,  $V_{CM} = 0V$ 

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
V <sub>IO</sub>		+V <sub>CC</sub> = 26V, -V <sub>CC</sub> = -4V,		-5.0	5.0	mV	1
		V <sub>CM</sub> = -11V		-7.0	7.0	mV	2, 3
		$+V_{CC} = 4V, -V_{CC} = -26V,$		-5.0	5.0	mV	1
	Input Offcot Voltage	V <sub>CM</sub> = 11V		-7.0	7.0	mV	2, 3
	Input Offset Voltage			-5.0	5.0	mV	1
				-7.0	7.0	mV	2, 3
		$\pm V_{CC} = \pm 5V$		-5.0	5.0	mV	1
		±vCC = ±2v		-7.0	7.0	mV	2, 3
±I <sub>IB</sub>		+V <sub>CC</sub> = 26V, -V <sub>CC</sub> = -4V,		-0.4	0.2	nA	1
		V <sub>CM</sub> = -11V, t ≤ 25mS		-10	50	nA	2
	Innut Bing Coment	1 < 05m2		-0.2	0.2	nA	1
	Input Bias Current	t ≤ 25mS		-10	50	nA	2
		+V <sub>CC</sub> = 4V, -V <sub>CC</sub> = -26V,		-0.2	1.2	nA	1
		V <sub>CM</sub> = 11V, t ≤ 25mS		-10	70	nA	2
I <sub>IO</sub>	Land Office to October	1.4050		-0.1	0.1	nA	1
	Input Offset Current	t ≤ 25mS		-20	20	nA	2
+PSRR	Power Supply Rejection Ratio	$+V_{CC} = 10V \text{ to } 20V, -V_{CC} = -15V$		80		dB	1, 2, 3
-PSRR	Power Supply Rejection Ratio	$+V_{CC} = 15V$ , $-V_{CC} = -10V$ to $-20V$		80		dB	1, 2, 3
CMR	Input Voltage Common Mode Rejection	V <sub>CM</sub> = -11V to +11V		80		dB	1, 2, 3
V <sub>IO Adj</sub> +	Adjustment for Input Offset Voltage			8.0		mV	1, 2, 3
V <sub>IO Adj</sub> -	Adjustment for Input Offset Voltage				-8.0	mV	1, 2, 3
I <sub>OS</sub> +	Output Short Circuit Current	t ≤ 25mS		-80		mA	1, 2, 3
I <sub>OS</sub> -	Output Short Circuit Current	t ≤ 25mS			80	mA	1, 2, 3
$I_{CC}$	Supply Current				3.5	mA	1, 2
	Supply Current				4.0	mA	3
$\Delta V_{IO}$ / $\Delta T$	Input Offcot Voltage	$25^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	See <sup>(1)</sup>	-30	30	μV/°C	2
	Input Offset Voltage	-55°C ≤ T <sub>A</sub> ≤ 25°C	See <sup>(1)</sup>	-30	30	μV/°C	3
+V <sub>OP</sub>	Output Voltage Swing	$R_L = 10K\Omega$		12		V	4, 5, 6
	Output Voltage Swing	$R_L = 2K\Omega$		10		V	4, 5, 6
-V <sub>OP</sub>	Output Voltage Swine	$R_L = 10K\Omega$			-12	V	4, 5, 6
	Output Voltage Swing	$R_L = 2K\Omega$			-10	V	4, 5, 6
+A <sub>VS</sub>	Open Lean Valtara Cair	$R_{\perp} = 2K\Omega$ ,	See <sup>(2)</sup>	50		K	4
	Open Loop Voltage Gain	$V_0 = 0$ to 10V	See <sup>(2)</sup>	25		K	5, 6
-A <sub>VS</sub>	Open Lean Valtara Cair	$R_L = 2K\Omega$ ,	See <sup>(2)</sup>	50		K	4
	Open Loop Voltage Gain	$V_0 = 0 \text{ to } -10V$	See <sup>(2)</sup>	25		K	5, 6
A <sub>VS</sub>	Open Loop Voltage Gain	$R_L = 10K\Omega, V_O = \pm 2V,$ $\pm V_{CC} = \pm 5V$	See <sup>(2)</sup>	20		K	4, 5, 6

Calculated parameter. For calculation use  $V_{IO}$  test at  $\pm V_{CC} = \pm 15V$  Datalog in K = V/mV.

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## **Electrical Characteristics AC Parameters**

The following conditions apply to all the following parameters, unless otherwise specified.

AC:  $V_{CC} = \pm 15V$ ,  $V_{CM} = 0V$ 

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
SR+	Claur Data	\/		7.0		V/µS	7
	Slew Rate	$V_I = -5V \text{ to } +5V$		5.0		V/µS	8A, 8B
SR-	Claur Data	$V_1 = +5V \text{ to } -5V$		7.0		V/µS	7
	Slew Rate	V <sub>1</sub> = +5V to -5V		5.0		V/µS	8A, 8B
TR <sub>TR</sub>	Transient Response Rise Time	$A_V = 1, V_I = 50 \text{mV},$ $C_L = 100 \text{pF}, R_L = 2 \text{K}\Omega$			200	nS	7, 8A, 8B
TR <sub>OS</sub>	Transient Response Overshoot	$A_V = 1, V_I = 50 \text{mV},$ $C_L = 100 \text{pF}, R_L = 2 \text{K}\Omega$			40	%	7, 8A, 8B
NI <sub>BB</sub>	Noise Broadband	BW of 10Hz to 15KHz			15	$\mu V_{RMS}$	7
NI <sub>PC</sub>	Noise Popcorn	BW of 10Hz to 15KHz, $R_S = 100K\Omega$			80	μV <sub>PK</sub>	7
+tS	Settling Time	A <sub>V</sub> = 1			1,50 0	nS	12
-tS	Settling Time	A <sub>V</sub> = 1			1,50 0	nS	12

## **Electrical Characteristics DC Drift Parameters**

The following conditions apply to all the following parameters, unless otherwise specified.

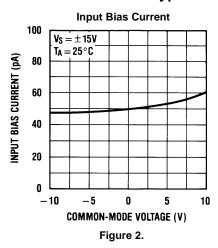
DC:  $V_{CC} = \pm 15V$ ,  $V_{CM} = 0V$ 

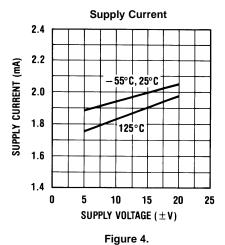
Delta Calculations performed at Group B, subgroup 5, Only

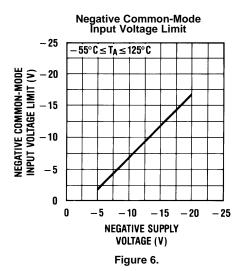
Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
V <sub>IO</sub>	Input Offset Voltage			-1.0	1.0	mV	1
$\pm I_{IB}$	Input Bias Current			-0.1	0.1	nA	1

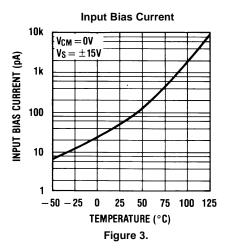


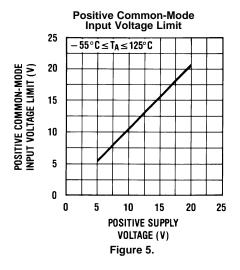
## **Typical Performance Characteristics**

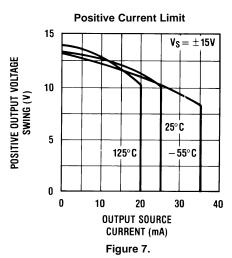






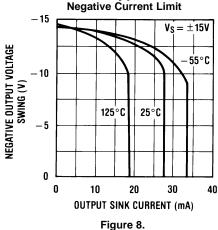


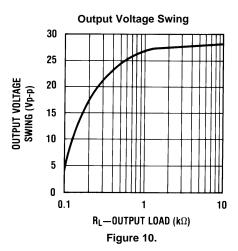


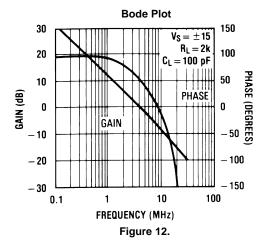


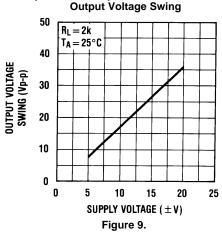
Instruments

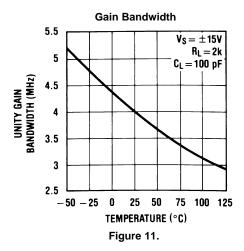
# Typical Performance Characteristics (continued) Negative Current Limit Output Voltage Swing

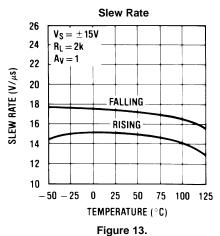






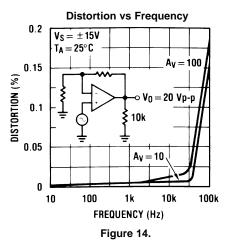


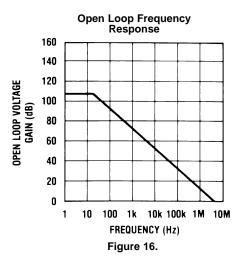


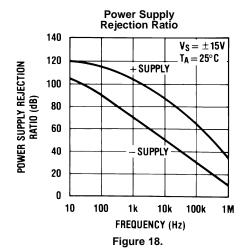


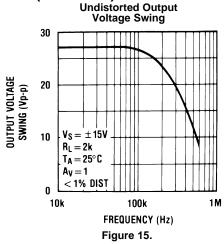


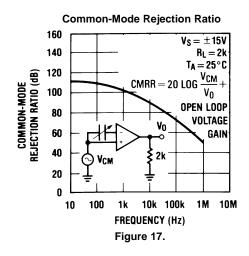
## **Typical Performance Characteristics (continued)**

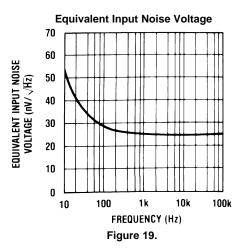






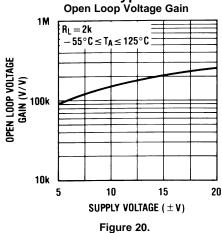


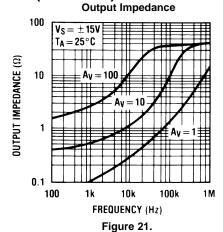


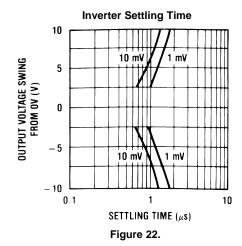


**INSTRUMENTS** 

# **Typical Performance Characteristics (continued)**

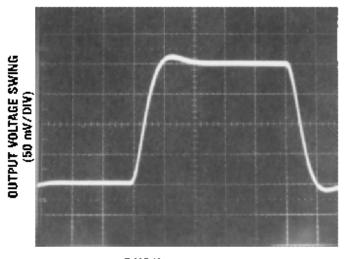


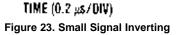


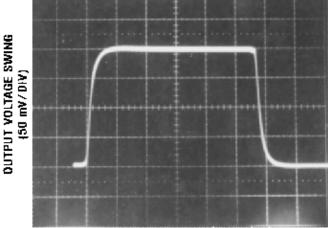


## **Pulse Response**

## $R_L=2 k\Omega, C_L10 pF$





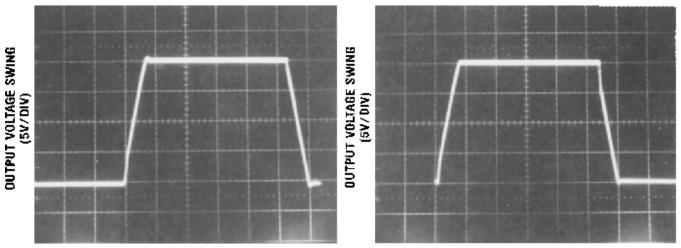


TIME (0.2 µs/DIV)

Figure 24. Small Signal Non-Inverting

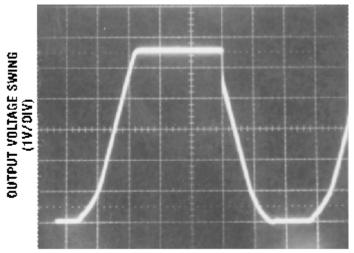


# **Pulse Response (continued)**



TIME (2 μS/DIV)
Figure 25. Large Signal Inverting

TIME (2 µs/DIV) Figure 26. Large Signal Non-Inverting



TIME (5  $\mu$ s/DIV) Figure 27. Current Limit (RL=100 $\Omega$ )



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### **APPLICATION HINTS**

The LF411JAN series of internally trimmed JFET input op amps (BI-FET II™) provide very low input offset voltage and ensured input offset voltage drift. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore, large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output; however, if both inputs exceed the limit, the output of the amplifier may be forced to a high state.

The amplifier will operate with a common-mode input voltage equal to the positive supply; however, the gain bandwidth and slew rate may be decreased in this condition. When the negative common-mode voltage swings to within 3V of the negative supply, an increase in input offset voltage may occur.

The LF411 is biased by a zener reference which allows normal circuit operation on ±4.5V power supplies. Supply voltages less than these may result in lower gain bandwidth and slew rate.

The LF411 will drive a 2  $k\Omega$  load resistance to ±10V over the full temperature range. If the amplifier is forced to drive heavier load currents, however, an increase in input offset voltage may occur on the negative voltage swing and finally reach an active current limit on both positive and negative swings.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

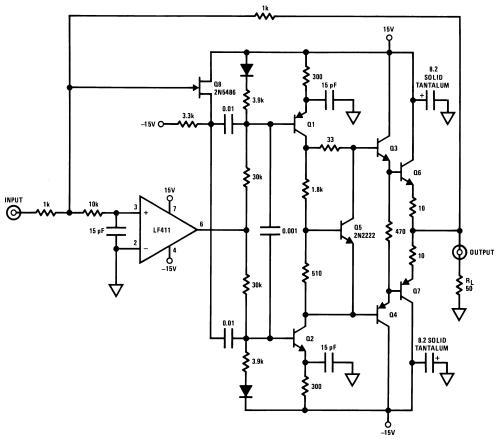
As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately 6 times the expected 3 dB frequency, a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.



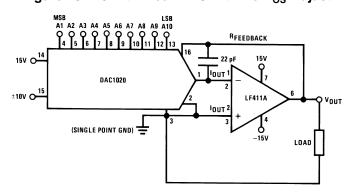
## **Typical Applications**

Figure 28. High Speed Current Booster



PNP=2N2905 NPN=2N2219 unless noted TO-5 heat sinks for Q6-Q7

Figure 29. 10-Bit Linear DAC with No  $V_{\rm OS}$  Adjust

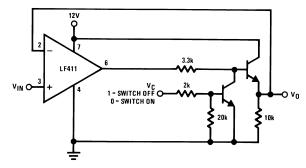


$$\begin{split} &V_{OUT} = -V_{REF} \left(\frac{A1}{2} + \frac{A2}{4} + \frac{A3}{8} + \cdots \frac{A10}{1024}\right) \\ &-10V \leq V_{REF} \leq 10V \\ &0 \leq V_{OUT} \leq -\frac{1023}{1024} V_{REF} \end{split}$$

where  $A_N=1$  if the  $A_N$  digital input is high  $A_N=0$  if the  $A_N$  digital input is low

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Figure 30. Single Supply Analog Switch with Buffered Output



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# **Table 2. Revision History**

Date Released	Revision	Section	Originator	Changes
10/11/05	А	New Release to corporate format	L. Lytle	1 MDS data sheet was converted into the corporate data sheet format. MDS MJLF411-X Rev 0C1 will be archived.
3/27/2013	А	All Sections		Changed layout of National Data Sheet to TI format





27-Oct-2016

### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
JM38510/11904BPA	LIFEBUY	CDIP	NAB	8		TBD	Call TI	Call TI	-55 to 125	JL411BPA Q JM38510/ 11904BPA ACO 11904BPA >T	
M38510/11904BPA	LIFEBUY	CDIP	NAB	8		TBD	Call TI	Call TI	-55 to 125	JL411BPA Q JM38510/ 11904BPA ACO 11904BPA >T	
M38510/11904BPX	LIFEBUY	CDIP	NAB	8		TBD	Call TI	Call TI	-55 to 125	JL411BPA Q JM38510/ 11904BPA ACO 11904BPA >T	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



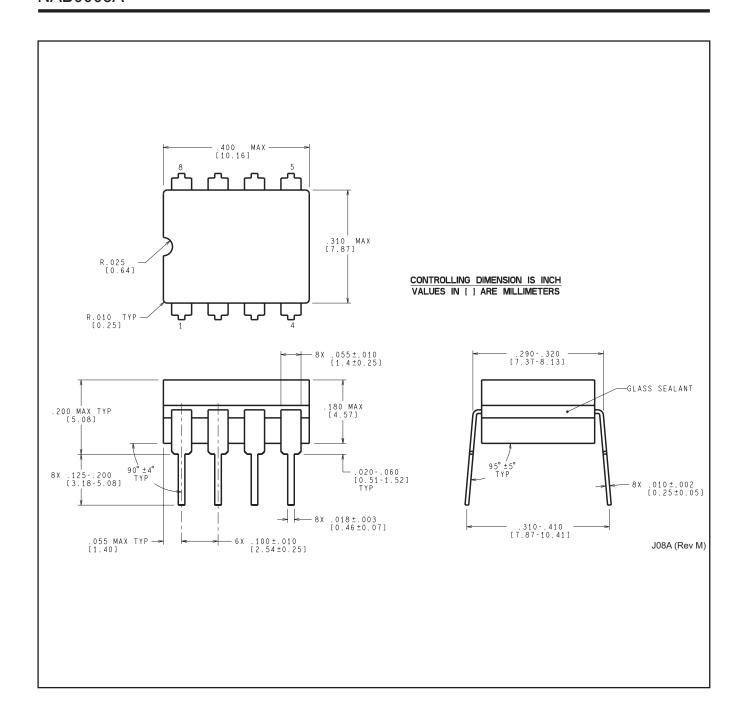
## **PACKAGE OPTION ADDENDUM**

27-Oct-2016

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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